

In the Claims:

Claim 1 (currently amended): A flash memory device, comprising:

a. a substrate;

b. at least one plurality of core stacks, wherein the at least one each core stack comprises:

- (1) a tunnel oxide layer on the substrate;
- (2) a first polysilicon layer on the tunnel oxide layer;
- (3) an anti-reflective interpoly layer on the first polysilicon layer; and
- (4) a transmissive second polysilicon layer on the anti-reflective

interpoly layer;

c. at least one plurality of source regions adjacent to the at least one plurality of core stacks; and

d. at least one plurality of drain regions adjacent to the at least one plurality of core stacks.

Claim 2 (currently amended): The flash memory device, as recited in Claim 1, wherein the at least one plurality of source regions and the at least one plurality of drain regions are formed by the method comprising the steps of:

a. depositing a layer of photoresist over the substrate and the at least one plurality of core stacks;

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- b. illuminating the layer of photoresist with a light;
- c. transmitting some of the light through the transmissive second polysilicon layer;
- d. preventing the reflection of the light at the anti-reflective interpoly layer;
- e. removing part of the photoresist layer; and
- f. implanting a dopant into the substrate.

Claim 3 (original): The flash memory device, as recited in Claim 2, wherein the light has a wavelength λ_1 , and wherein the anti-reflective interpoly layer has an index of refraction n and a thickness d , and wherein the light has an integer number m wavelengths incident upon the anti-reflective interpoly layer, and wherein

$$d \cong \frac{(m + \frac{1}{2})\lambda_1}{2n}, \text{ where } m = 0, 1, 2, \dots$$

Claim 4 (original): The flash memory device, as recited in Claim 2, wherein the light has a wavelength λ_1 , and wherein the anti-reflective interpoly layer has an index of refraction n , and a thickness d , wherein

$$d \cong \frac{\lambda_1}{4n}.$$

Claim 5 (original): The flash memory device, as recited in Claim 4, wherein the anti-reflective interpoly layer is made of silicon oxynitride (SiON).

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Claim 6 (original): The flash memory device, as recited in Claim 5, wherein the thickness of the anti-reflective interpoly layer is between about 300 to 400 Å thick.

Claim 7 original): The flash memory device, as recited in Claim 2, wherein the step of depositing the layer of photoresist, deposits the photoresist onto a surface of the transmissive second polysilicon layer.

Claim 8 (original): The flash memory device, as recited in Claim 1, wherein the anti-reflective interpoly layer is made of silicon oxynitride.

Claim 9 (original): The flash memory device, as recited in Claim 8, wherein the thickness of the anti-reflective interpoly layer is between about 300 to 400 Å thick.

Claims 10-15 (canceled)